Signetics

Linear Products

DESCRIPTION

THE NE/SA5217 is a 75MHz postamplifier system designed to accept low level high-speed signals. These signals are converted into a TTL level at the output. The NE5217 can be DC coupled with the previous transimpedance stage using NE5210, NE5211 or NE5212 transimpedance amplifiers. The main difference between the NE5217 and the NE5214 is that the NE5217 does not make the output of A1 and input of A2 accessible, instead, it brings out the output of A2 and the input of A8 thus activating the on-chip Schmidt trigger function by connecting two external capacitors. The result is that a much longer string of 1's and 0's, in the bit stream, can be tolerated. This "system on a chip" features an auto-zeroed first stage with noise shaping, a symmetrical limiting second stage, and a matched rise/fall time TTL output buffer. The system is user-configurable to provide adjustable input thresholds and hysteresis. The threshold capability allows the user to maximize signal-tonoise ratio, insuring a low Bit Error Rate (BER). An Auto-Zero loop can be used to minimize the number of external coupling capacitors to one. A signal absent flag indicates when signals are below threshold. Additionally, the low signal condition forces the overall TTL output to a logical Low level. User interaction with this "jamming" system is available. The NE/SA5217 is packaged in a standard 20-pin surface-mount package and typically consumes 42mA from a standard 5V supply. The NE/SA5217 is designed as a companion to the NE/ SA5211/5212 transimpedance amplifiers. These differential preamplifiers may

NE/SA5217 Fiber Optic Postamplifier with Link Status Indicator

Objective Specification

be directly coupled to the post-amplifier inputs. The NE/SA5212/5217 or NE/ SA5211/5217 combinations convert nanoamps of photodetector current into standard digital TTL levels.

FEATURES

- Postamp for the NE/SA5211/5212 preamplifier family
- Wideband operation: typical 75MHz (100MBaud NRZ)
- Interstage filtering/equalization possible
- Single 5V supply
- Low signal flag
- Low signal output disable
- Link status threshold and hysteresis programmable
- LED driver (normally ON with above threshold signal)
- Fully differential for excellent PSRR
- Auto-zero loop for DC offset cancellation
- 2kV ElectroStatic Discharge (ESD) protection

APPLICATIONS

- Fiber optics
- Communication links in Industrial and/or Telecom environment with high EMI/RFI
- Local Area Networks (LAN)
- Metropolitan Area Networks (MAN)
- Synchronous Optical Networks (SONET)
- RF limiter
- Good for 2²³-1 pseudo random number sequence

PIN CONFIGURATION

D ¹ Package								
	LED 1	20 IN 18						
	CPKDET 2	19 IN 1A						
	THRESH 3	18 CAZP						
	GNDA 4	17 CAZN						
	FLAG 5	16 OUT 28						
	JAM	15 INea						
	Vcco 🖸	14 OUT 2A						
	V _{CCA} 🖪	13 IN 8A						
	GND _D 9	12 RHYST						
	Vour 10	11 R PKDET						
NO	TE:	C0153215						
1. 5 DIN	SOL — Release	ed in large SO package only.						
NO.	SYMBOL	DESCRIPTION						
1	LED	Output for the LED driver. Open collector output transistor with 125Ω series limiting resistor. An above threshold signal turns this						
2	CPKDET	transistor ON. Capacitor for the peak detector. The value of this capacitor de- termines the detector response						
3	THRESH	time to the signal, supplementing the internal 10pF capacitor. Peak detector threshold resistor. The value of this resistor deter- mines the threshold level of the						
4	GNDA	peak detector. Device analog ground pin.						
5	FLAG	Peak detector digital output. When this output is LOW, there is data present above the threshold. This pin is normally connected to the IAM pin and						
6	JAM	has a fanout of two. Input to inhibit data flow. Send- ing the pin HIGH forces TTL DATA OUT ON, Pin 10, Low. This pin is normally connected to the FLAG pin and is TTL-						
7	VccD	compatible. Power supply pin for the digital						
8	VCCA	portion of the chip. Power supply pin for the analog						
9	GNDD	portion of the chip. Device digital ground pin.						
10	VOUT	TTL output pin with a fanout of five.						
11	RPKDET	Peak detector current resistor. The value of this resistor determines the amount of discharge current available to the peak detector capacitor, C_{PKDET} .						

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE			
20-Pin Plastic SOL	0 to +70°C	NE5217D			
20-Pin Plastic SOL	-40°C to +85°C	SA5217D			

Objective Specification

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PIN CONFIGURATION (cont.)

PIN NO.	SYMBOL	DESCRIPTION
12	R _{HYST}	Peak detector hysteresis resistor. The value of this resistor determines the amount of hysteresis in the peak detector.
13	IN _{BA}	Non-inverting input to amplifier A8.
14	OUT _{2A}	Non-inverting output of amplifier A2.
15	IN _{BB}	Inverting input to amplifier A8.
16	OUT28	Inverting output of amplifier A2.
17	CAZN	Auto-Zero capacitor pin (Negative terminal). The value of this capacitor determines the low-end frequency response of the preamp A1.
18	Cazp	Auto-Zero capacitor pin (Positive terminal). The value of this capacitor determines the low-end frequency response of the preamp A1.
19	IN1A	Non-inverting input of the preamp A1.
20	IN _{1B}	Inverting input of the preamp A1.

BLOCK DIAGRAM



NE/SA5217

ABSOLUTE MAXIMUM RATINGS

00000		RAT			
STMBOL	PARAMETER	NE5214	SA5214		
VCCA	Power supply	+6	+6	V	
V _{CCD}	Power supply	+6	+6	V	
TA	Operating ambient temperature range	0 to +70	-40 to +85	°C	
Tj	Operating junction temperature range	-55 to +150	-55 to +150	°C	
T _{STG}	Storage temperature range	-65 to +150	-65 to +150	°C	
PD	Power dissipation	300	300	mW	
V _{IJ}	Jam input voltage	-0.5 to 5.5	-0.5 to 5.5	v	

RECOMMENDED OPERATING CONDITIONS

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STMBUL	PARAMETER	NE5214	SA5214	UNIT	
V _{CCA}	Supply voltage	4.75 to 5.25	4.75 to 5.25	v	
V _{CCD}	Power supply	4.75 to 5.25	4.75 to 5.25	v	
T _A	Ambient temperature range	0 to +70	-40 to +85	°C	
TJ	Operating junction temperature range	0 to +95	-40 to +110	°C	
PD	Power dissipation	250	250	mW	

DC ELECTRICAL CHARACTERISTICS Min and Max limits apply over the operating temperature range at $V_{CCA} = V_{CCD} = +5.0V$ unless otherwise specified. Typical data applies at $V_{CCA} = V_{CCD} = +5.0V$ and $T_A = 25^{\circ}C$.

	PARAMETER		NE5214						
SYMBOL		TEST CONDITIONS	Min	Тур	Max	Min	Тур	Max	UNIT
ICCA	Analog supply current			30	36		30	37.2	mA
ICCD	Digital supply current (TTL, Flag, LED)			10	13.3		10	13.5	mA
V _{I1}	A1 input bias voltage (+/- inputs)	3.16	3.4	3.63	3.13	3.4	3.65	v	
V _{O1}	A1 output bias voltage (+/- outputs)	3.17	3.8	4.45	3.10	3.8	4.50	V	
A _{V1}	A1 DC gain (without Auto-Zero)			30			30		dB
A1 _{PSRR}	A1 PSRR (VCCA, VCCD)	$V_{CCA} = V_{CCD} = 4.75$ to 5.25V		60			60		dB
A1 _{CMRR}	A1 CMRR	∆V _{CM} = 200mV		60			60		dB
V _{I8}	A8 input bias voltage (+/- inputs)	3.59	3.7	3.85	3.7	3.86	V		
V _{OH}	High-level TTL output voltage	I _{OH} = -200μA	2.4	3.4		2.4	3.4		V
V _{OL}	Low-level TTL output voltage	I _{OL} = 8mA		0.3	0.4		0.3	0.4	V
юн	High-level TTL output current	V _{OUT} = 2.4V		-40	-26		-40	-24.4	μA
IOL	Low-level TTL output current	V _{OUT} = 0.4V	8.0	30		7.0	30		mA
los	Short-circuit TTL output current	V _{OUT} = 0.0V		-95			-95		mA
VTHRESH	Threshold bias voltage	Pin 3 Open		0.75			0.75		V
VRPKDET	RPKDET	Pin 11 Open		0.72			0.72		V
VRHYST	RHYST bias voltage	Pin 12 Open		0.72			0.72		V
VIHJ	High-level jam input voltage		2.0			2.0			V
VILJ	Low-level jam input voltage				0.8			0.8	V
JIHI	High-level jam input current	V _{IJ} = 2.7V			20			30	μA

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DC ELECTRICAL CHARACTERISTICS (Continued) Min and Max limits apply over the operating temperature range at $V_{CCA} = V_{CCD} = +5.0V$ unless otherwise specified. Typical data applies at $V_{CCA} = V_{CCD} = +5.0V$ and $T_A = 25^{\circ}C$.

SYMBOL	PARAMETER	TEST CONDITIONS	NE5214			SA5214			
			Min	Тур	Max	Min	Тур	Max	UNIT
اال	Low-level jam input current	V _{IJ} = 0.4V	-450	-240		-485	-240		μA
VOHF	High-level flag output voltage	I _{OH} = -80μA	2.4	3.8		2.4	3.8		V
VOLF	Low-level flag output voltage	$I_{OL} = 3.2 \text{mA}$		0.33	0.4		0.33	0.4	V
IOHF	High-level flag output current	V _{OUT} = 2.4V		-18	-5.3		-18	-5	mA
IOLF	Low-level flag output current	$V_{OUT} = 0.4V$	3.6	10		3.25	10		mA
ISCF	Short-circuit flag output current	V _{OUT} = 0.0V	-60	-40	-25	-61	-40	-26	mA
LEDH	LED ON maximum sink current	V _{LED} = 3.0V	13	22	80	8	22	80	mA

AC ELECTRICAL CHARACTERISTICS Min and Max limits apply over the operating temperature range at $V_{CCA} = V_{CCD} = +5.0V$ unless otherwise specified. Typical data applies at $V_{CCA} = V_{CCD} = +5.0V$ and $T_A = 25^{\circ}C$.

	PARAMETER	TEST CONDITIONS		NE5214							
SYMBOL				Min	Тур	Max	Min	Тур	Max	UNIT	
fop	Maximum operating frequency	Tes	Test Circuit			75		60	75		MHz
BW _{A1}	Small signal bandwidth (differential OUT ₁ /IN ₁)	Tes	Test Circuit			75			75		MHz
VINH	Maximum Functional A1 input signal (single ended)	Tes	st Circuit			1.6			1.6		V _{P-P}
VINL	Maximum Functional A1 input signal (single ended)	Tes	Test Circuit ¹			12			12		mV _{P-P}
R _{IN1}	Input resistance (differential at IN1)					1200			1200		Ω
C _{IN1}	Input capacitance (differential at IN1)					2			2		pF
R _{IN2}	Input resistance (differential at IN2)					1200			1200		Ω
C _{IN2}	Input capacitance (differential at IN2)					2			2		рF
R _{OUT1}	Output resistance (differential at OUT1)					25			25		Ω
C _{OUT1}	Output capacitance (differential at OUT ₁)					2			2		pF
V _{HYS}	Hysteresis voltage range	Test circ	uit, T _A = 25°C	;		3			3		mV _{P-P}
VTHR	Threshold voltage range (FLAG ON)	Test circuit, @ 50MHz R _{BHYST} ≕5k R _{THRESH} = 47k				12			12	mV _{P-P}	
t _{TLH}	TTL Output Rise Time 20% to 80%	Te	st circuit			1.3			1.3		ns
t _{THL}	TTL Output Fall Time 80% to 20%	Test circuit				1.2			1.2		ns
tRFD	t _{TLH} /t _{THL} mismatch	1				0.1			0.1		ns
tpwp	Pulse width distortion of output	$50mV_{P,P}, 1010input$ Distortion = $\frac{T_H - T_L}{T_H + T_L} 10^2$			2.5				2.5		%

NOTE:

1. The NE/SA5217 is capable of detecting a much lower input level. Operation under 12mVp.p cannot be guaranteed by present day automatic testers.

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TYPICAL PERFORMANCE CHARACTERISTICS



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THEORY OF OPERATION AND APPLICATION INFORMATION

The NE 5217 post amplifier system is a highly integrated chip that provides up to 60dB of gain at 60MHz, to bring mV level signals up to TTL levels.

The NE5217 contains eight amplifier blocks (see Block Diagram). The main signal path is made up of a cascade of limiting stages: A1, A2 and A8. The A3-A4-A7 path performs a wideband full-wave rectification of the input signal with adjustable hysteresis and decay times. It outputs a TTL HIGH on the "FLAG" output (Pin 5) when the input is below a user adjustable threshold. An on-chip LED driver turns the external LED to the ON state when the input signal is above the threshold. In a typical application the "FLAG" output is tied back to the "JAM" input; this forces the TTL data OUT into a LOW state when no signal is present at the input.

An auto zero loop allows the NE5217 to be directly connected to a transimpedance amplifier such as the NE5210, NE5211, or NE5212 without coupling capacitors. This auto-zero loop cancels the transimpedance amplifiers's DC offset, the NE5217 A1 offset, and the data-dependent offset in the PIN diode/transimpedance amplifier combination. For more information on the NE5217 Theory of Operation, please refer to paper titled "A Low Cost 100 MBaud Fiber-Optic Receiver" by W. Mack et a1. A typical application of the NE5217 post amplifier is depicted in Figure 2. The system uses the NE5211 transimpedance amplifier which has a 28k differential transimpedance gain and a –3dB bandwidth of 1400Hz. This typical application is optimized for a 50 Mb/s Non Return to Zero (NRZ) bit stream.

As the system's gain bandwidth product is very high, it is crucial to employ good RF design and printed circuit board layout techniques to prevent the system from becoming unstable.

For more information on this application, please refer to Application Brief AB 1432.

